



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re Patent Application of)	Art Unit: 2822	
Shunpei YAMAZAKI et/al.)	Examiner: M. Wilczewski	
Serial No. 08/691,434√)	CERTIFICATE OF MAILING	
Filed: August 2, 1996		I hereby certify that this correspondence is being deposited with	
For: METHOD OF FABRICATING)	The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 2023), on 213	
SEMICONDUCTOR DEVICES AND)		
APPARATUS FOR PROCESSING A)		
SEMICONDUCTOR	`		

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents Washington, D.C. 20231

Sir:

In response to the Office Action dated August 13, 2002 please amend the aboveidentified application as follows:

IN THE CLAIMS:

Please cancel claims 76-77, 79, 84-85 and 90-91 and amend claims 16, 56, and 74-75 as follows:



(Amended) An apparatus for processing a semiconductor comprising: a first vacuum chamber;

an ion introducing apparatus for doping a semiconductor layer formed over a substrate with a dopant impurity through an insulating film comprising oxide provided over said semiconductor layer;

an etching apparatus for etching said insulating film comprising oxide to expose a surface of said semiconductor layer, said etching apparatus connected to said ion introducing apparatus through said first vacuum chamber;

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